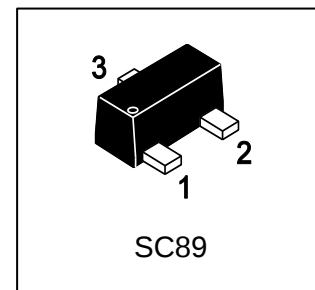


LBC847BTT1G

General Purpose Transistors NPN Silicon

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.

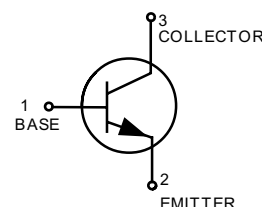


2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC847BTT1G	1F	4000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	45	V
Collector–Base Voltage	VCBO	50	V
Emitter–Base Voltage	VEBO	6	V
Collector Current — Continuous	IC	100	mA



4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	200 1.6	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) @ TA = 25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 2)	RθJA	400	°C/W
Junction and Storage temperature range	TJ,Tstg	–55~+150	°C

1. FR-4 @ min pad.

2. FR-4 @ 1.0 × 1.0 in pad.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)
OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 10 mA)	VBR(CEO)	45	-	-	V
Collector–Emitter Breakdown Voltage (IC = 10 μ A, VEB = 0)	VBR(CES)	50	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μ A)	VBR(CBO)	50	-	-	V
Emitter–Base Breakdown Voltage (IE = 1.0 μ A)	VBR(EBO)	6	-	-	V
Collector Cutoff Current (VCB = 30 V)	ICBO	-	-	15	nA
(VCB = 30 V, TA = 150°C)		-	-	5	μ A

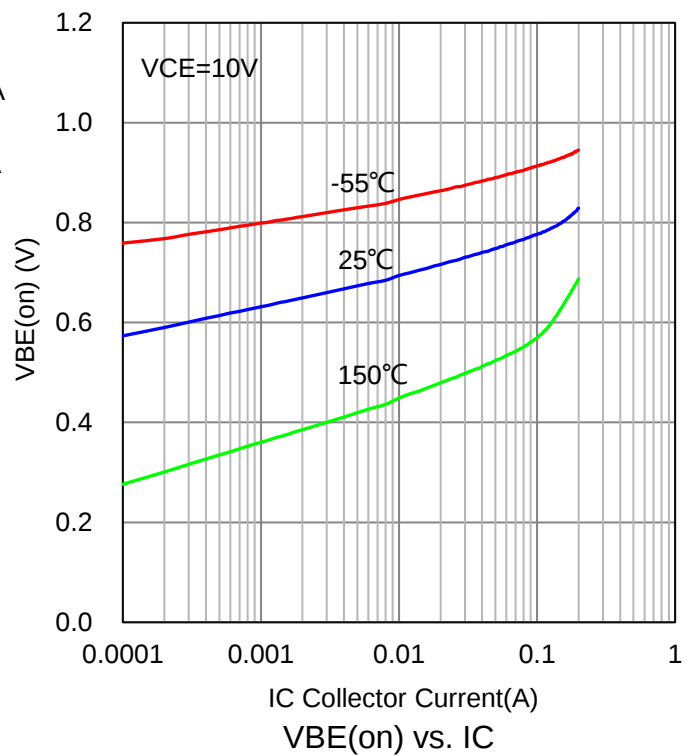
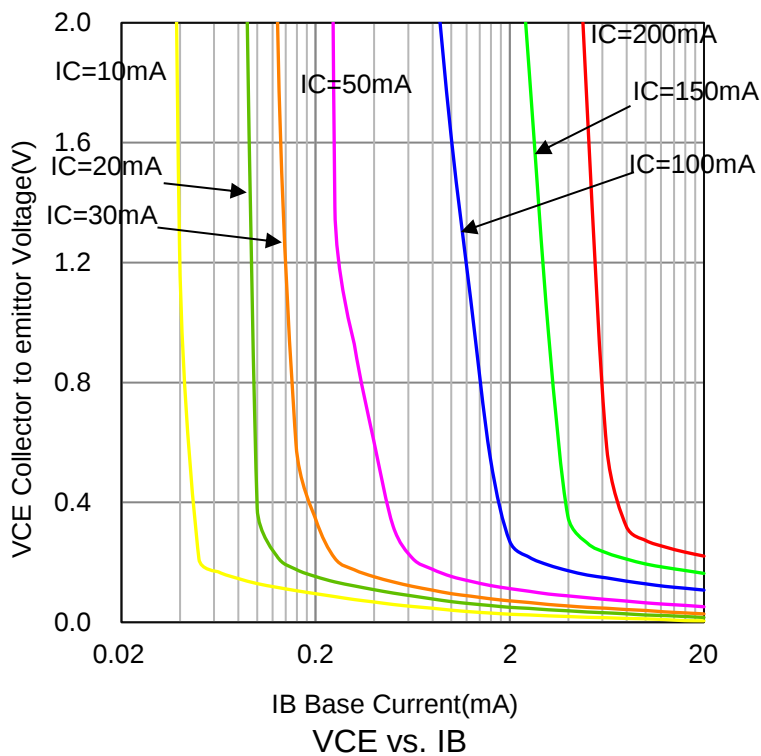
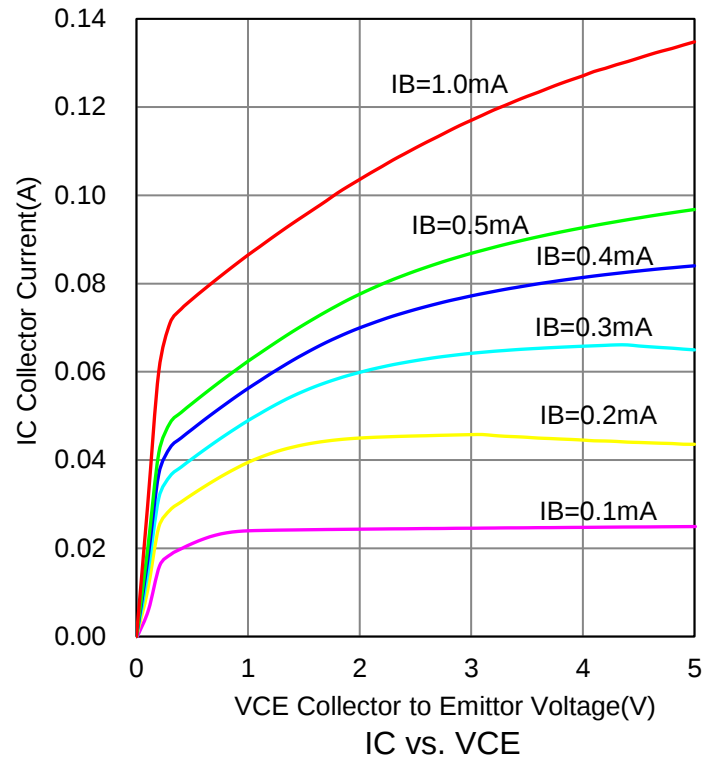
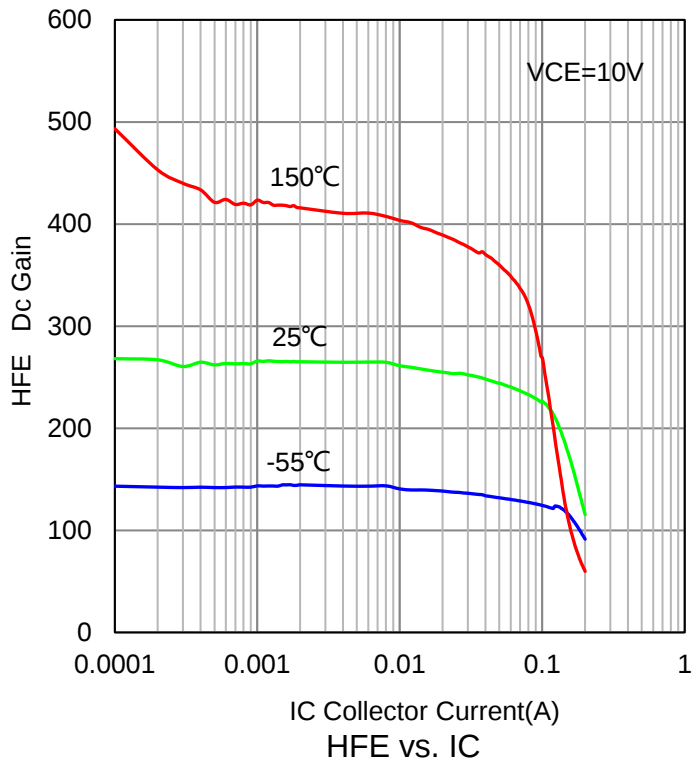
ON CHARACTERISTICS

DC Current Gain (IC = 10 μ A, VCE = 5.0 V) (IC = 2.0 mA, VCE = 5.0 V)	HFE	-	150	-	
		200	290	450	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VCE(sat)	-	-	0.25	V
		-	-	0.6	
Base–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VBE(sat)	-	0.7	0.9	V
		-	0.9	1.2	
Base–Emitter Voltage (IC = 2.0 mA, VCE = 5.0 V) (IC = 10 mA, VCE = 5.0 V)	VBE(on)	580	660	700	mV
		-	-	770	

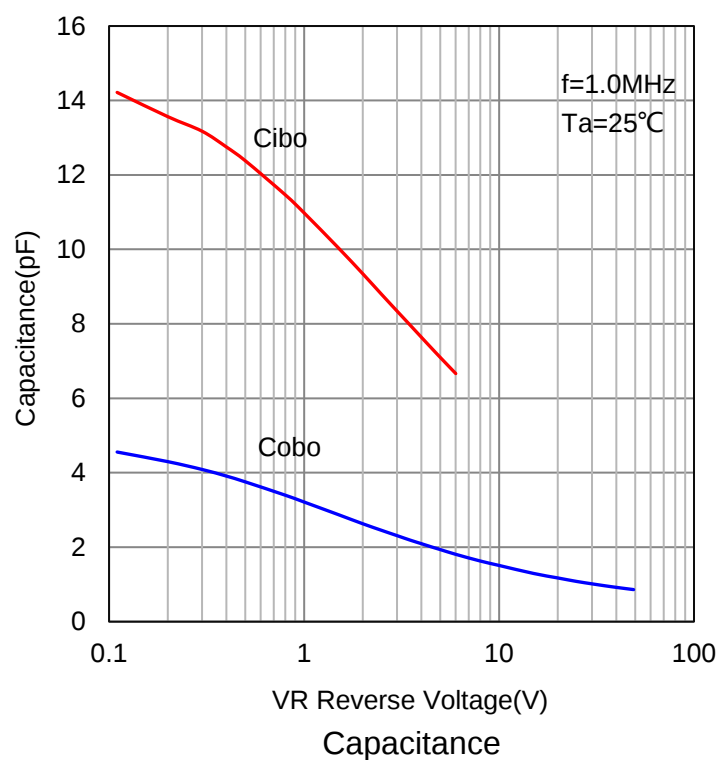
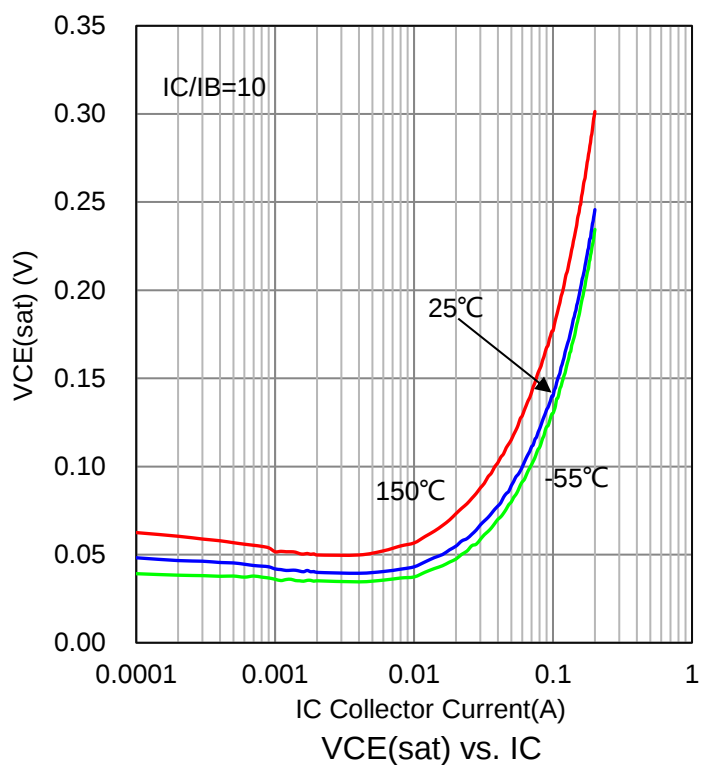
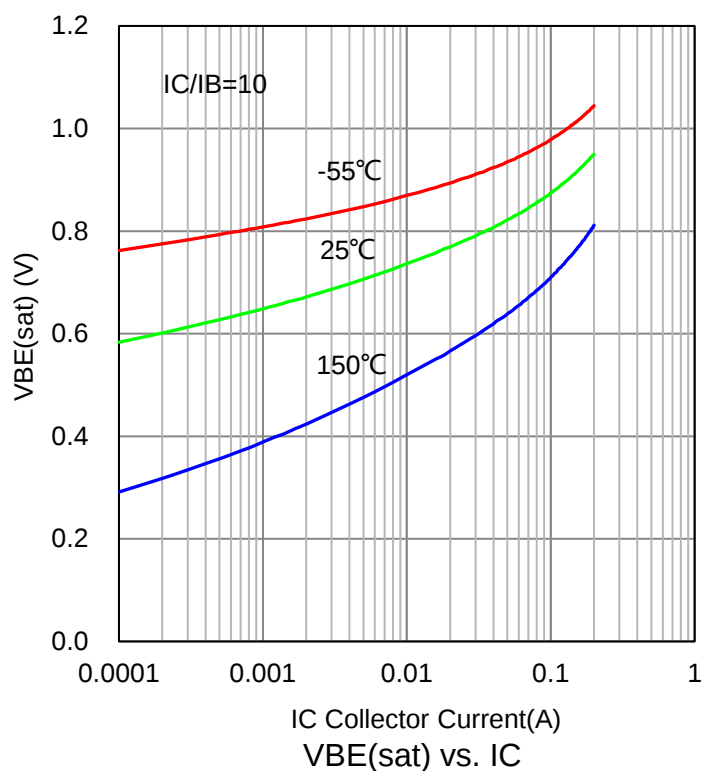
SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 V, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = 10 V, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 k Ω f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

6.ELECTRICAL CHARACTERISTICS CURVES



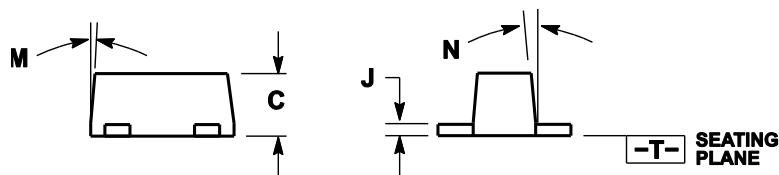
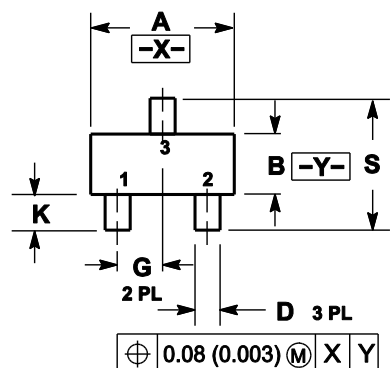
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7.OUTLINE AND DIMENSIONS

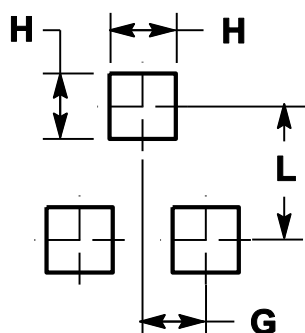
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50BSC			0.020BSC		
H	0.53REF			0.021REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.02
L	1.10REF			0.043REF		
M	---	---	10°	---	---	10°
N	---	---	10°	---	---	10°
S	1.50	1.60	1.70	0.059	0.063	0.067

8.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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